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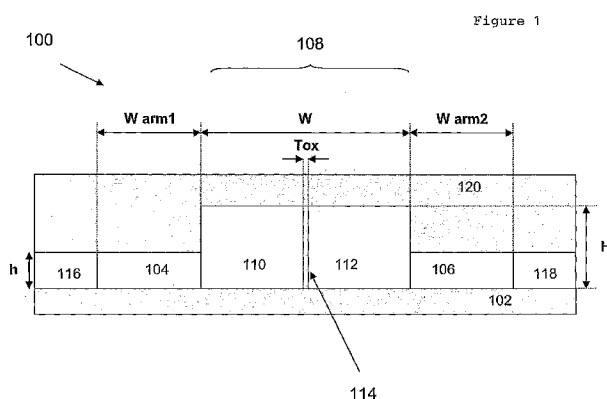
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(54) Title: AN ELECTRO-OPTIC DEVICE AND A METHOD FOR MANUFACTURING THE SAME



(57) Abstract: An electro-optic device is disclosed. The electro-optic device includes an insulating layer, a first semiconducting region disposed above the insulating layer and being doped with doping atoms of a first conductivity type, a second semiconducting region disposed above the insulating layer and being doped with doping atoms of a second conductivity type and an electro-optic active region disposed above the insulating layer and between the first semiconducting region and the second semiconducting region. The electro-optic active region includes a first semiconducting partial active region being doped with doping atoms of the first conductivity type, a second semiconducting partial active region being doped with doping atoms of the second conductivity type and an insulating structure between the first semiconducting partial active region and the second semiconducting partial active region, wherein the insulating structure extends perpendicular to the surface of the insulating layer such that there is no overlap of the first semiconducting partial active region and the second semiconducting partial active region in the direction perpendicular to the surface of the insulating layer. A method for manufacturing an electro-optic device is also disclosed.

WO 2009/020432 A1